THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application

Inventor:

Tatau NISHINAGA

Group Art Unit: 1765

Appln. No.:

09/511,912

Examiner: M. Anderson

Filed:

February 23, 2000

For:

A METHOD FOR FORMING A SINGLE CRYSTALLINE FILM

TTTGG

CERTIFICATION UNDER 37 CFR §1.97(e)(1)

Assistant Commissioner of Patents Washington, DC 20231

Dear Sir:

In fulfillment of 37 CFR 1.97(c)(1) and 1.97(e)(1), it is hereby certified that each item of information contained in the attached Information Disclosure Statement was first cited in any communication (see the attached copy of a German Office Action dated June 21, 2004) from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this Information Disclosure Statement.

Respectfully submitted,

Date: September 21, 2004

James E. Ledbetter

Registration No. 28,732

JEL/spp

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INFORMATION DISCLOSURE STATEMENT

Assistant Commissioner of Patents Washington, DC 20231

Dear Sir:

Pursuant to Rules 56 and 99, Applicants hereby call the attention of the Patent Office to the art listed on the attached Form PTO 1449. All of these references were cited in a German Office Action dated June 21, 2004 (English translation attached) except for US '473. US '473 corresponds to DE '186.

Applicants present this art so that the Patent Office may, in the first instance, determine any relevancy thereof to the presently claimed invention, see Beckman Instruments, Inc. v. Chemtronics, Inc., 439 F.2d 1369, 1380, 165 USPQ 355, 364 (5th Cir. 1970). Also see Patent Office Rules 104 and 106. Applicants respectfully request that this art be expressly considered during the prosecution of this application and made of record herein and appear among the "References Cited" on any patent to issue herefrom.

Respectfully submitted,

Date: September 21, 2004

James E. Ledbetter Registration No. 28,732

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EXAMINER: Initial if citation is considered, draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.